



CLIPPEDIMAGE= JP408203847A
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TITLE: MANUFACTURE OF SEMICONDUCTOR DEVICE

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INVENTOR-INFORMATION:
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ABSTRACT:

PURPOSE: To form silicon thin film with an improved coverage for a contact hole with a high aspect ratio.

CONSTITUTION: After forming a contact hole 3A at silicon oxide film 2 on silicon substrate 1, polycrystalline silicon film 4 is formed on the side wall as a contact hole 3B with an aspect ratio of approximately 10. Then, SiH<SB>4</SB> is supplied as a feed gas under surface reaction speed-controlling conditions using the LPCVD method and at the same time Cl<SB>2</SB> gas as an etching gas is supplied under supply speed-controlling conditions and then the contact hole is buried by amorphous silicon film 5. Then, heat treatment is made to form polycrystalline silicon film.

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